

55. (Amended) A method of forming a transistor gate comprising:

forming a gate and a gate oxide layer in overlapping relation, the gate having opposing edges and a center therebetween, the gate oxide having a center and outwardly exposed opposing edges laterally aligned with the edges of the gate; and

concentrating at least one of chlorine or fluorine in the gate oxide layer having the outwardly exposed opposing edges and within the overlap more proximate at least one of the outwardly exposed oxide gate edges than the center.

New Claims

Please add new claims 76 and 77 as follows:

76. The method of claim 51 wherein the forming the gate comprises forming the gate elevationally above the gate oxide layer.

77. The method of claim 51 wherein the forming the gate comprises forming an entirety of the gate proximate the gate oxide layer.